

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7484	((438/30) or (257/E21.143) or (257/E21.413) or (438/158)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/09/30 09:13
L2	4048	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	USPAT	OR	ON	2008/09/30 09:13
L3	1843	L2 and oxide and (Chromium Aluminum Molybdenum)	USPAT	OR	ON	2008/09/30 09:13
L4	6313	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/09/30 09:13
L5	738	L4 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/30 09:13
L6	282	L4 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride) and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/30 09:13
S1	2	"20050173732"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:42

S2	8466	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:44
S3	3086	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	USPAT	OR	ON	2007/04/01 02:44
S4	2156	S3 and oxide and (Cr\$3 Mo\$3 Al\$3)	USPAT	OR	ON	2007/04/01 02:46
S5	1453	S3 and oxide and (Chromium Aluminum Molybdenum)	USPAT	OR	ON	2007/04/01 02:47
S6	862	S5 and @ad<"20020115"	USPAT	OR	ON	2007/04/01 02:47
S7	96	S6 and (low near resistivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:34
S12	6	"5905589"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20
S13	32	"5062689"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20
S14	5387	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/01 23:36
S15	1390	S14 AND TFT and Source and data and gate and insulating and pixel and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:37

S16	1062	S14 AND TFT and Source and data and gate and insulating and pixel and electrode and (Chromium Aluminum Molybdenum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
S17	564	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
S18	255	S17 and @ad<"20020115"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
S19	255	S17 and @ad<"20020115"	US-PGPUB; USPAT	OR	ON	2007/04/01 23:38
S20	286	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
S21	267	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40

S22	193	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride) and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40
S23	137	(opaque with improve) and LCD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/14 13:11
S24	132	(opaque with improve) and LCD	US-PGPUB; USPAT	OR	ON	2007/10/14 13:11
S25	5708	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/14 23:00
S28	880	pixel metal oxide opaque block light\$3 tft lcd	US-PGPUB; USPAT	AND	ON	2008/02/17 15:49
S29	314	pixel metal oxide opaque block light\$3 tft lcd	USPAT	AND	ON	2008/02/17 15:50
S30	7071	((438/30) or (257/E21.143) or (257/E21.413) or (438/158)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/17 17:54

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